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Zhitang Song**
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Introduction

The 2016 International Workshop on Information Storage/Tenth International Symposium on Optical Storage (IWIS/ISOS 2016) was held 10–13 April 2016 in Changzhou City, Jiangsu Province, China, under the auspices of the National Natural Science Foundation of China, Chinese Academy of Sciences (CAS), and Science and Technology Commission of Shanghai Municipality. The workshop/symposium was organized by Shanghai Institute of Microsystem and Information Technology (SIMIT), CAS, Shanghai Institute of Optics and Fine Mechanics (SIOM), CAS and Jiangsu University of Technology. More than 100 scientists, technologists, and experts from universities, research institutes, and industries of 8 countries and regions participated in the workshop/symposium, which provided a forum for reviewing recent progress and exchanging information in a wide range of topics including materials, physics, devices, measurement and manufacturing technologies in information storage. 92 papers were presented at the workshop/symposium, including 35 as oral presentations and 57 as posters.

As predecessors of this workshop/symposium, the previous nine symposia of the ISOS series were successfully held in Shanghai 1988, Chongqing 1990, Kunming 1992, Shenzhen 1996, Shanghai 2000, Wuhan 2002, Zhanjiang 2005, Wuhan 2008 and Shanghai 2012, respectively. From the 8th symposium, the ISOS meeting extended its topics, and a workshop on information storage was added due to the merging of data storage technologies in recent years. The workshop/symposium promoted discussions on both the theoretical aspects and practical applications of information storage and strengthened cooperation and friendship in the semiconductor, optical and magnetic memory communities.

We are very grateful to the members of the International Advisory Committee, the Local Organizing and Technical Committee, as well as the Secretariat for their fruitful work in the preparation and operation of the workshop/symposium. Thanks are also extended to our invited speakers and all of the contributing authors for their elaborate preparation of the presentations or manuscripts. Finally, we gratefully acknowledge the sponsors and cosponsors, without whose support we could not have held such a successful workshop/symposium.

Fuxi Gan
Zhitang Song

